

# Avionics Pulsed Power Transistor, 700 Watts, 1.03-1.09 GHz, 32 $\mu$ S Pulse, 2% Duty

12/10/01

Rev. 0

PH1090-700B

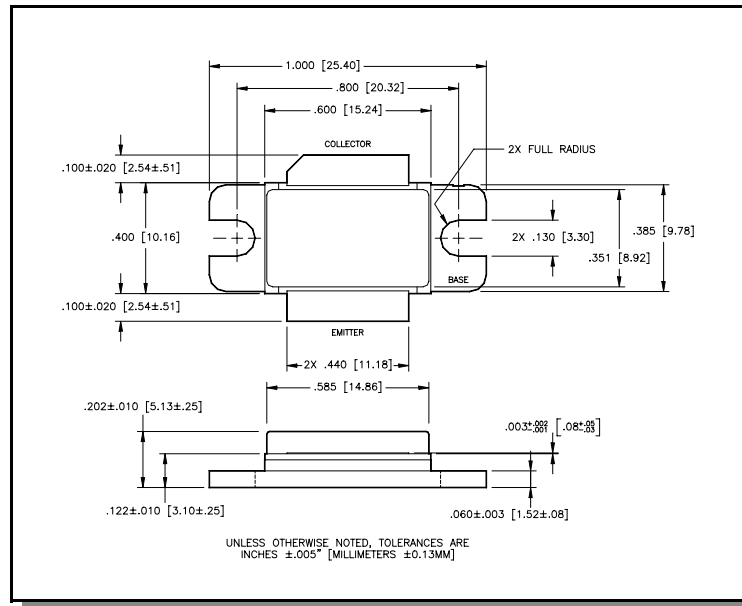
## Features

- Designed for Mode-S IFF Applications
- NPN Silicon Microwave Power Transistor
- Common Base Configuration
- Broadband Class C Operation
- High Efficiency Interdigitated Geometry
- Gold Metalization System
- Internal Input and Output Impedance Matching
- Hermetic Metal/Ceramic Package

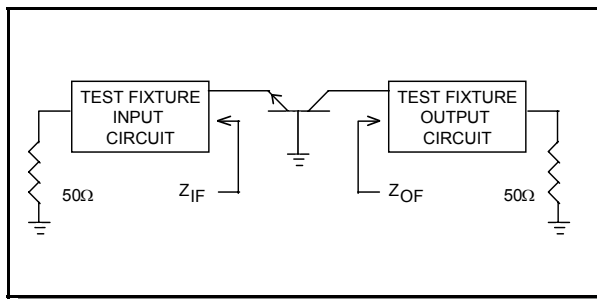
## Absolute Maximum Ratings @ 25 °C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	$V_{CES}$	65	V
Emitter-Base Voltage	$V_{EBO}$	3.0	V
Collector Current (Peak)	$I_C$	35	A
Dissipated Power (Standard Pulse Cond.)	$P_{TOT}$	2.9	kW
Dissipated Power (Mode-S Pulse Train)	$P_{TOT}$	700	W
Storage Temperature	$T_{STG}$	-65 to +200	°C
Junction Temperature	$T_J$	200	°C

## Outline Drawing



## Broadband Test Fixture Impedances



F (GHz)	$Z_{IF}$ ( $\Omega$ )	$Z_{OF}$ ( $\Omega$ )
1.03	1.1 -j1.4	1.2 -j0.8
1.06	1.1 -j1.2	1.0 -j0.7
1.09	1.0 -j1.0	0.8 -j0.7

## Electrical Characteristics at 25°C

**Standard Pulse Condition: 32 $\mu$ S Pulse Width, 2% Duty Cycle**

**Peak Power: 700 Watts**

Parameter	Symbol	Test Conditions	Min	Max	Units
Collector-Emitter Breakdown Voltage	BVCES	IC = 250 mA	80	-	V
Collector-Emitter Leakage Current	ICES	VCE = 50 V	-	25	mA
Thermal Resistance	RTH(JC)	V <sub>CC</sub> =50 V, P <sub>out</sub> =700 W, F=1.03, 1.09 GHz Pulse Conditions: 32 $\mu$ s, 2%	-	0.06	°C/W
Power Gain	GP	V <sub>CC</sub> =50 V, P <sub>out</sub> =700 W, F=1.03, 1.09 GHz Pulse Conditions: 32 $\mu$ s, 2%	7.5	-	dB
Collector Efficiency	$\eta$	V <sub>CC</sub> =50 V, P <sub>out</sub> =700 W, F=1.03, 1.09 GHz Pulse Conditions: 32 $\mu$ s, 2%	50	-	%
Input Return Loss	RL	V <sub>CC</sub> =50 V, P <sub>out</sub> =700 W, F=1.03, 1.09 GHz Pulse Conditions: 32 $\mu$ s, 2%	-10	-	dB
Load Mismatch Tolerance	VSWR-T	V <sub>CC</sub> =50 V, P <sub>out</sub> =700 W, F=1.03, 1.09 GHz Pulse Conditions: 32 $\mu$ s, 2%	-	5.0:1	-
Load Mismatch Stability	VSWR-S	V <sub>CC</sub> =50 V, P <sub>out</sub> =700 W, F=1.03, 1.09 GHz Pulse Conditions: 32 $\mu$ s, 2%	-	1.5:1	-

**Mode-S Pulse Train: 48 Pulses of 32 $\mu$ S “on”, 18 $\mu$ S “off” repeated every 24 mS, 6.4% Overall Duty Cycle\*\***

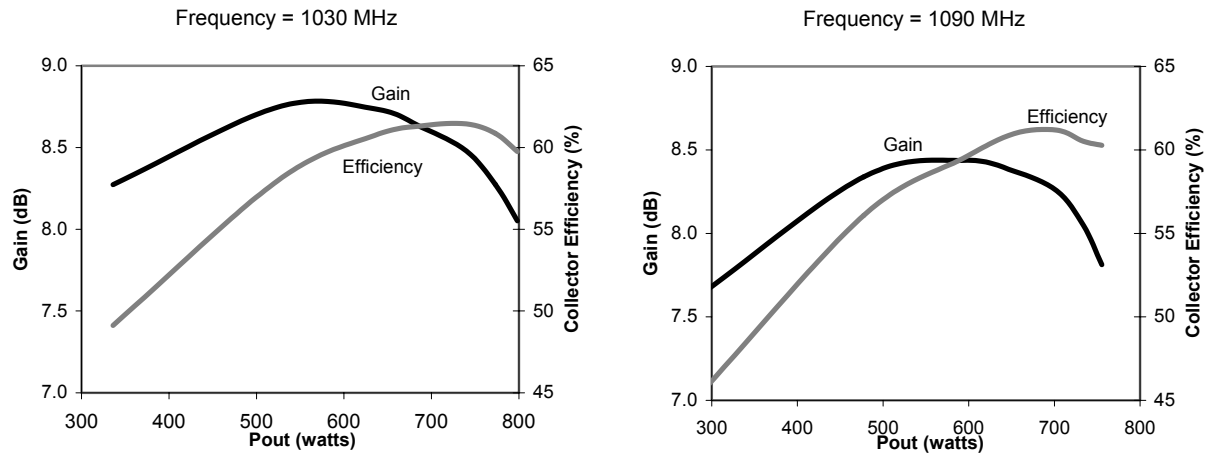
**Peak Power: 450 Watts**

Parameter	Symbol	Test Conditions	Typical	Units
Thermal Resistance	RTH(JC)	V <sub>CC</sub> =45v, P <sub>out</sub> =450 W, F=1.03, 1.09 GHz Mode-S Pulse Train	0.20	°C/W
Power Gain	GP	V <sub>CC</sub> =45v, P <sub>out</sub> =450 W, F=1.03, 1.09 GHz Mode-S Pulse Train	8.0	dB
Collector Efficiency	$\eta$	V <sub>CC</sub> =45v, P <sub>out</sub> =450 W, F=1.03, 1.09 GHz Mode-S Pulse Train	55	%
Input Return Loss	RL	V <sub>CC</sub> =45v, P <sub>out</sub> =450 W, F=1.03, 1.09 GHz Mode-S Pulse Train	-13	dB
Load Mismatch Tolerance	VSWR-T	V <sub>CC</sub> =45v, P <sub>out</sub> =450 W, F=1.03, 1.09 GHz Mode-S Pulse Train	2:1	-
Load Mismatch Stability	VSWR-S	V <sub>CC</sub> =45v, P <sub>out</sub> =450 W, F=1.03, 1.09 GHz Mode-S Pulse Train	1.5:1	-

\*\* Please note, the standard PH1090-700B device will be tested in accordance with the specifications defined for the Standard Pulse Condition (32 $\mu$ S, 2%)

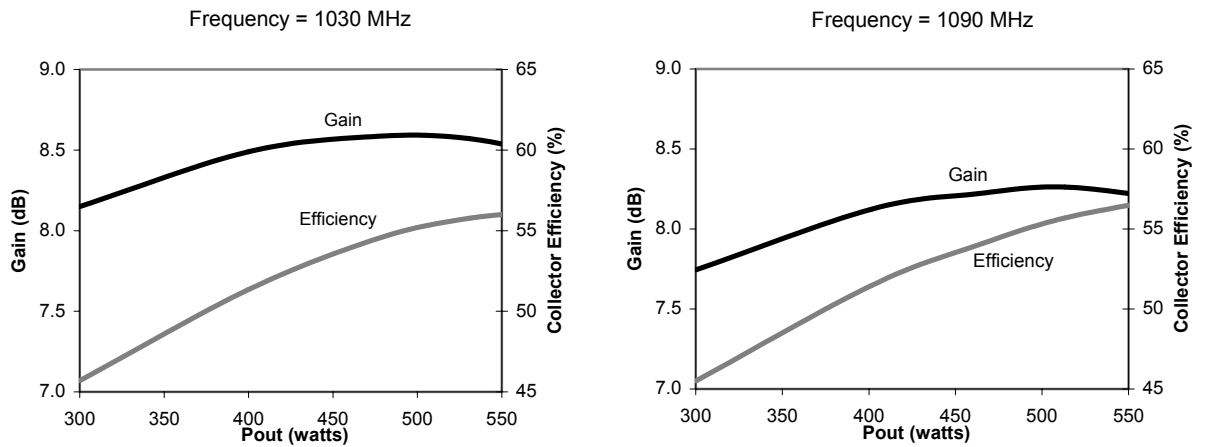
### Gain & Efficiency vs P<sub>OUT</sub>

V<sub>cc</sub> = 50V, Pulse Width = 32μS, Duty Cycle = 2%

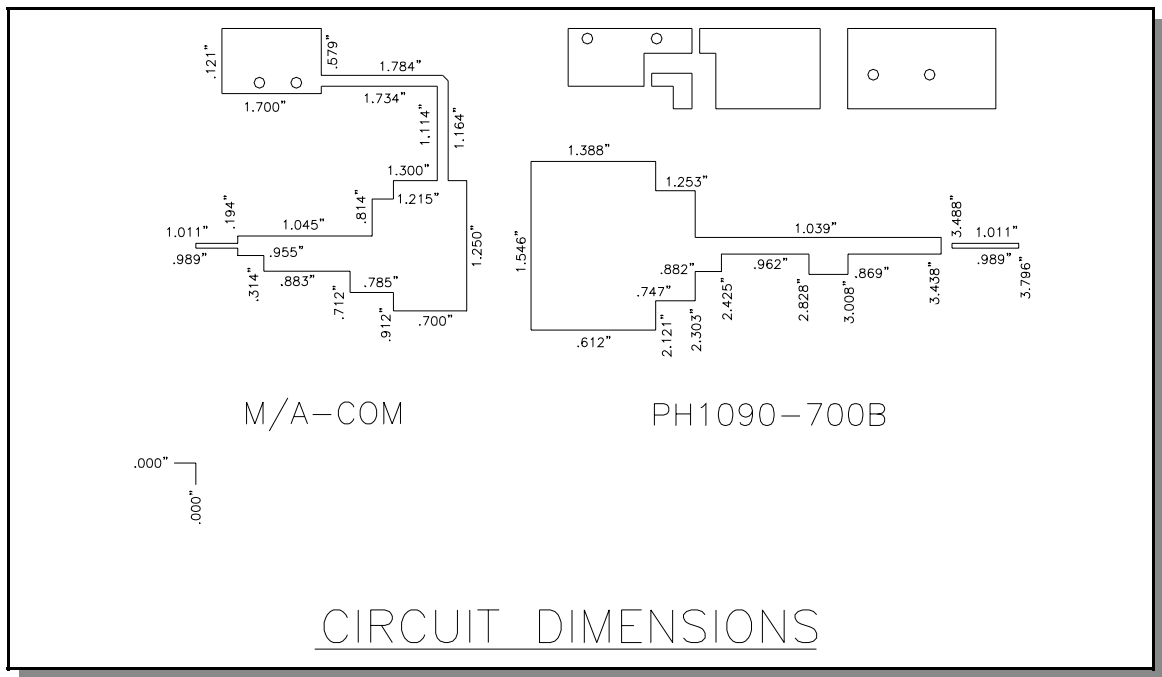


### Gain & Efficiency vs P<sub>OUT</sub>

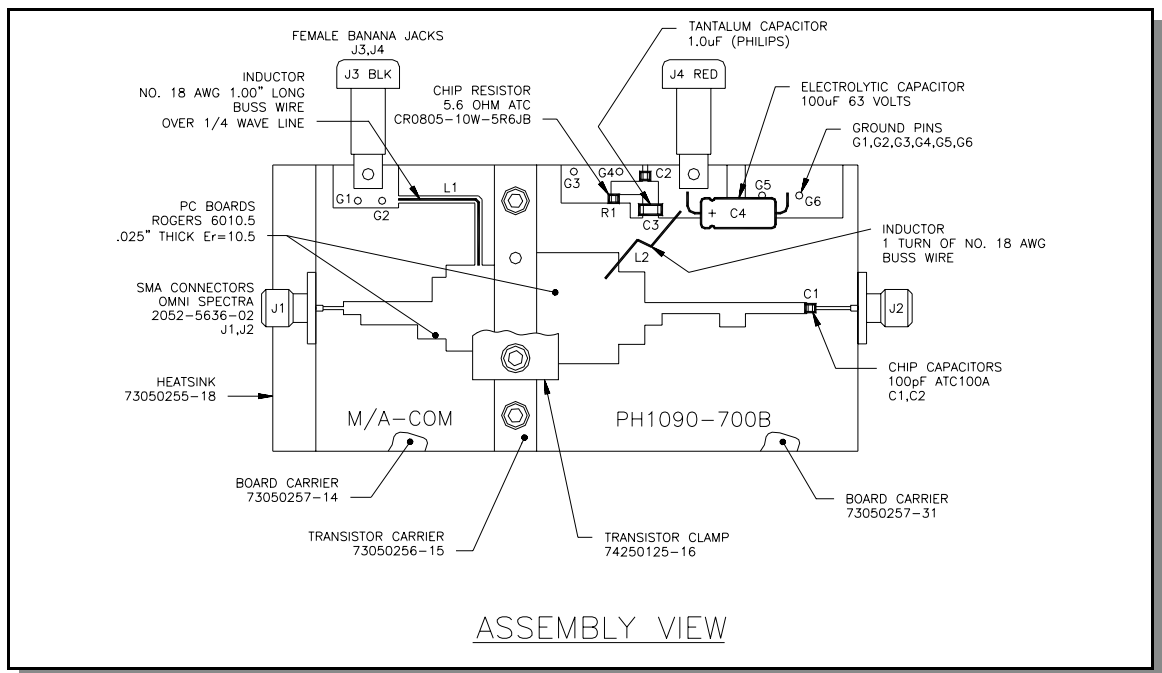
V<sub>cc</sub> = 45V, Mode-S Pulse Train



### Broadband Circuit Dimensions



### Broadband Assembly Diagram



Specifications subject to change without notice.

- North America: Tel. (800) 366-2266
- Asia/Pacific: Tel. +81-44-844-8296, Fax +81-44-844-8298
- Europe: Tel. +44 (1344) 869 595, Fax +44 (1344) 300 020

Visit [www.macom.com](http://www.macom.com) for additional data sheets and product information.

